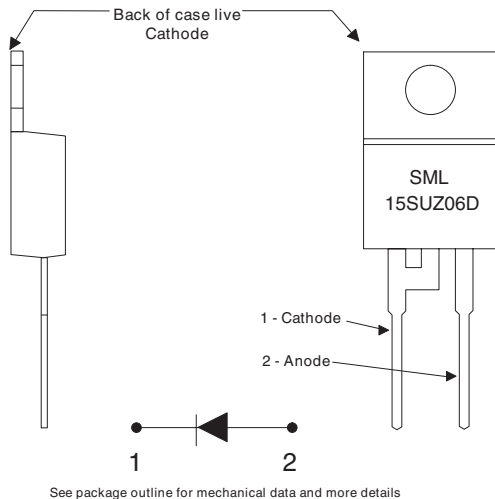


Ultrafast Recovery Diode 600 Volt, 15 Amp



TO220 Package

Key Parameters

V_R	(max)	600V
V_F	(typ)	2.0V
I_F	(max)	15A
t_{rr}	(max)	35ns

TECHNOLOGY

The planar passivated and standard ultrafast recovery diode features a triple charge control action utilising Semelab's graded Buffer Zone technology combined with low emitter efficiency and local lifetime control techniques.

BENEFITS

- Very fast recovery for low switching losses
- Ultra soft recovery with low EMI generation
- High dynamic ruggedness under all conditions
- Low temperature dependency
- Low on-state losses with positive temperature coefficient
- Stable blocking voltage and low leakage current
- Avalanche rated for high reliability circuit operation

APPLICATIONS

- Freewheeling Diode for IGBTs and MOSFETs
- Uninterruptible Power Supplies UPS
- Switch Mode Power Supplies SMPS
- Inverse and Clamping Diode
- Snubber Diode
- Fast Switching Rectification

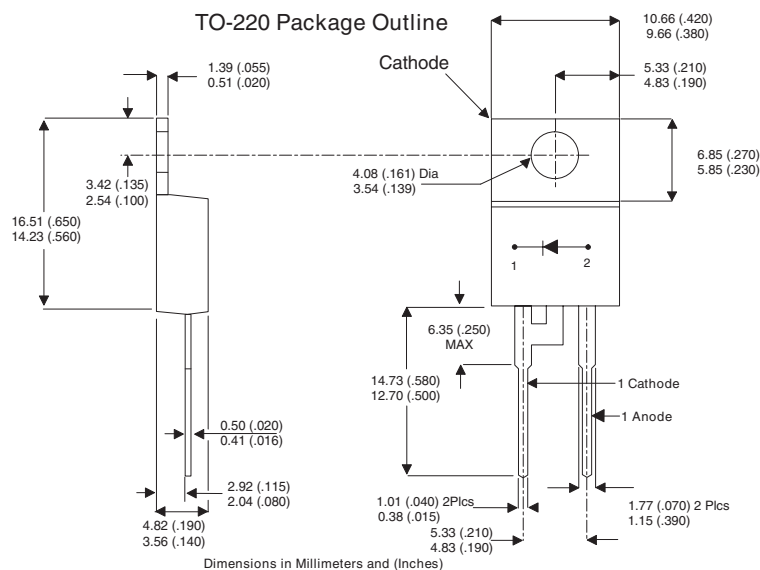
ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V_{RRM}	Peak Repetitive Reverse Voltage	600V
V_R	DC Reverse Blocking Voltage	600V
I_{FAV}	Average Forward Current @ T _C = 85°C	15A
$I_{FSM(surge)}$	Repetitive Forward Current	40A
$I_{FS(surge)}$	Non-Repetitive Forward Current	150A
P_D	Power Dissipation @ T _C = 85°C	30W
W_{AVL}	Avalanche Energy	10mJ
T _J , T _{STG}	Operating & Storage Junction Temperature	-55 to 150°C

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
STATIC ELECTRICAL CHARACTERISTIC					
V _F * Forward Voltage Drop	I _F = 15A T _J = 25°C		2	2.25	V
	I _F = 15A T _J = 125°C		2.15		
	I _F = 5A T _J = 25°C		1.45		
I _R Leakage Current	V _R = 600V T _J = 25°C		0.4	200	μA
	V _R = 600V T _J = 125°C		0.2	2	mA
C _T Junction Capacitance	V _R = 200V T _J = 25°C		11		pF
DYNAMIC ELECTRICAL CHARACTERISTIC					
Q _{rr} Reverse Recovery Charge	V _R = 300V I _F = 15A d _i / d _t = 800A/μs T _J = 25°C		0.41		μC
I _{rr} Reverse Recovery Current			18		A
t _{rr} Reverse Recovery Time			45		nsec
Q _{rr} Reverse Recovery Charge	V _R = 300V I _F = 15A d _i / d _t = 800A/μs T _J = 125°C		0.58		μC
I _{rr} Reverse Recovery Current			22		A
t _{rr} Reverse Recovery Time			54		nsec
t _{rr} Reverse Recovery Time	V _R = 50V I _F = 1A d _i / d _t = 100A/μs T _J = 25°C		35		nsec
THERMAL AND MECHANICAL CHARACTERISTICS					
R _{θjc} Junction to Case Thermal Resistance				2.2	°C/W
T _L Lead Temperature				300	°C
L _S Stray Inductance			10		nH
Torque Mounting Torque				0.7	N.m



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